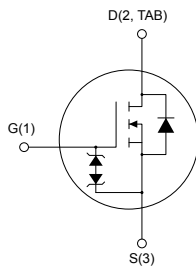


Automotive-grade N-channel 650 V, 365 mΩ typ., 9 A MDmesh DM6 Power MOSFET in a DPAK package



DPAK


AM01475V1



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STD9N65DM6AG	650 V	440 mΩ	9 A

- AEC-Q101 qualified 
- Fast-recovery body diode
- Lower R_{DS(on)} per area vs previous generation
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM6 fast-recovery diode series. Compared with the previous MDmesh fast generation, DM6 combines very low recovery charge (Q_{rr}), recovery time (t_{rr}) and excellent improvement in R_{DS(on)} per area with one of the most effective switching behaviors available in the market for the most demanding high-efficiency bridge topologies and ZVS phase-shift converters.

Product status link

[STD9N65DM6AG](#)

Product summary⁽¹⁾

Order code	STD9N65DM6AG
Marking	9N65DM6
Package	DPAK
Packing	Tape and reel

1. The HTRB test was performed at 80% V_{(BR)DSS} in compliance with AEC-Q101 rev. C. All the other tests were performed according to rev. D.

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	9	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	5.7	A
$I_D^{(1)}$	Drain current (pulsed)	28	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	89	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	50	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	100	
T_J	Operating junction temperature range	-55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature range		

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 9\text{ A}$, $di/dt \leq 800\text{ A}/\mu\text{s}$, $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.
3. $V_{DS} \leq 520\text{ V}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-case}}$	Thermal resistance junction-case	1.4	$^\circ\text{C}/\text{W}$
$R_{thj\text{-pcb}}^{(1)}$	Thermal resistance junction-pcb	50	

1. When mounted on FR-4 board of inch^2 , 2oz Cu.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or non-repetitive (pulse width limited by $T_J\text{ max}$)	2.5	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 100\text{ V}$)	400	mJ

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 4. On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = 650\text{ V}$			5	μA
		$V_{GS} = 0\text{ V}, V_{DS} = 650\text{ V}, T_C = 100\text{ °C}^{(1)}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			± 5	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.25	4	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 4.5\text{ A}$		365	440	m Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz}, V_{GS} = 0\text{ V}$	-	510	-	pF
C_{oss}	Output capacitance		-	36	-	pF
C_{rss}	Reverse transfer capacitance		-	0.4	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }520\text{ V}, V_{GS} = 0\text{ V}$	-	97	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}, \text{open drain}$	-	5.7	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}, I_D = 9\text{ A}, V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	11.7	-	nC
Q_{gs}	Gate-source charge		-	3.3	-	nC
Q_{gd}	Gate-drain charge		-	5.1	-	nC

1. $C_{oss\text{ eq.}}$ is defined as the constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}, I_D = 4.5\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$	-	7.8	-	ns
t_r	Rise time		-	3.6	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	27	-	ns
t_f	Fall time		-	10	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		9	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		28	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 9\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,	-	80		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60\text{ V}$	-	290		nC
I_{RRM}	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	7.2		A
t_{rr}	Reverse recovery time	$I_{SD} = 9\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,	-	132		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$	-	656		nC
I_{RRM}	Reverse recovery current	(see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	10		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

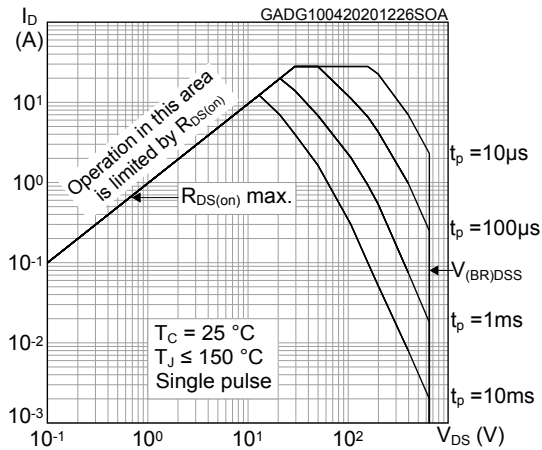


Figure 2. Maximum transient thermal impedance

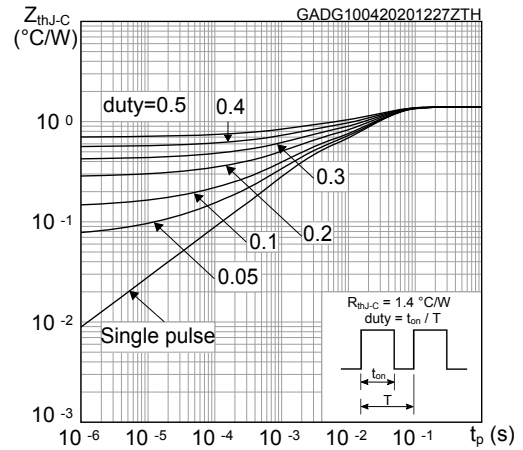


Figure 3. Typical output characteristics

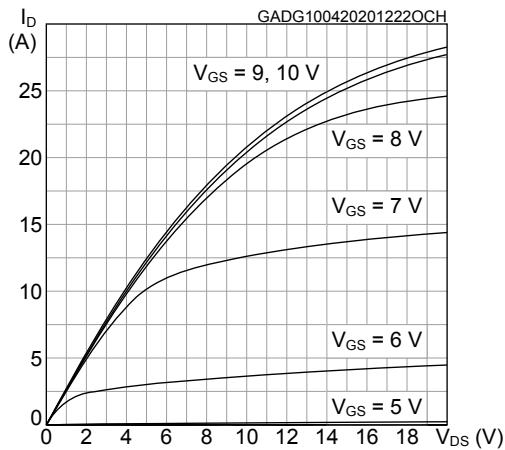


Figure 4. Typical transfer characteristics

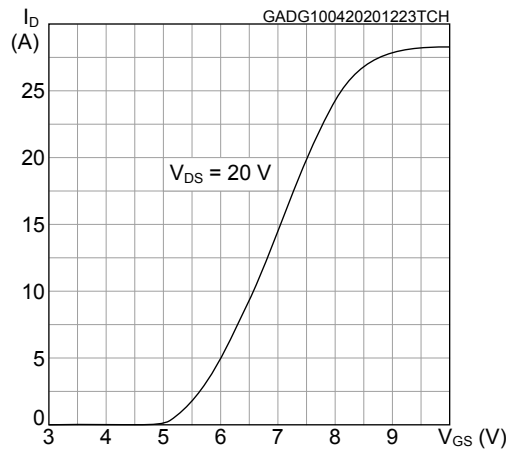


Figure 5. Typical drain-source on-resistance

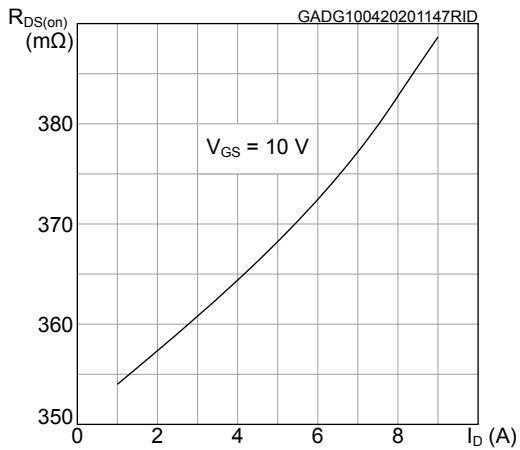


Figure 6. Typical gate charge characteristics

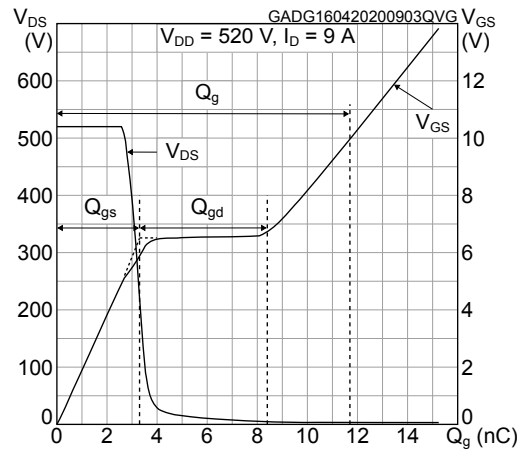


Figure 7. Typical capacitance characteristics

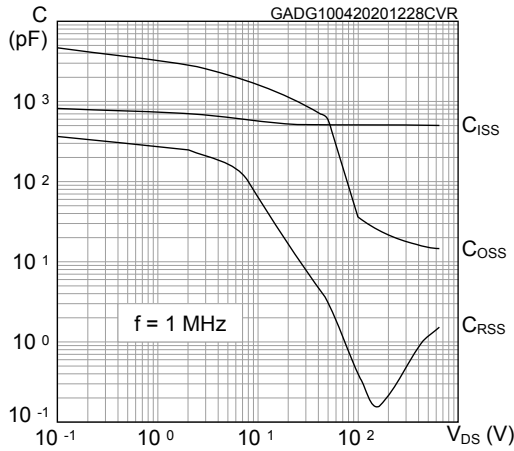


Figure 8. Normalized gate threshold vs temperature

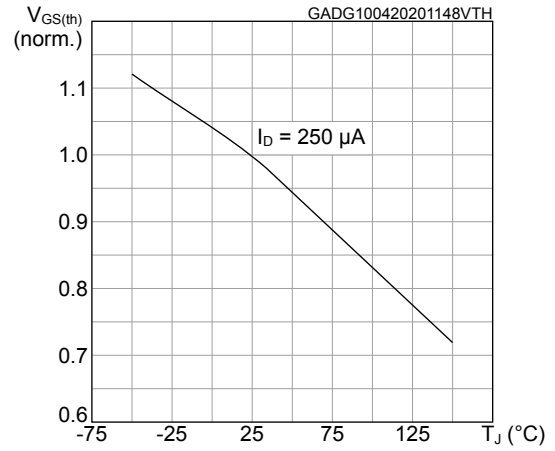


Figure 9. Normalized on-resistance vs temperature

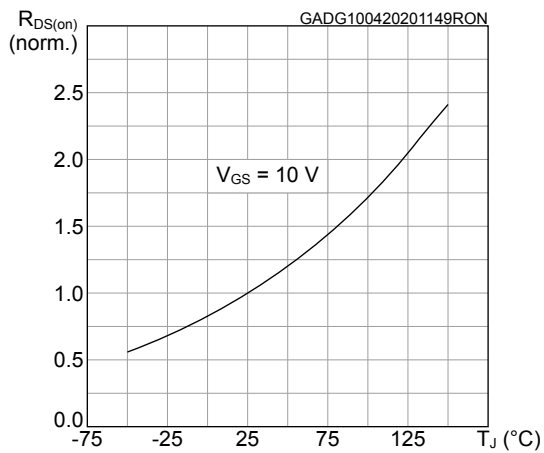


Figure 10. Typical output capacitance stored energy

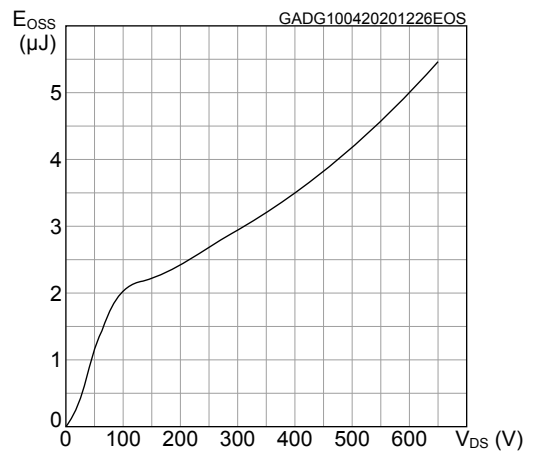


Figure 11. Normalized breakdown voltage vs temperature

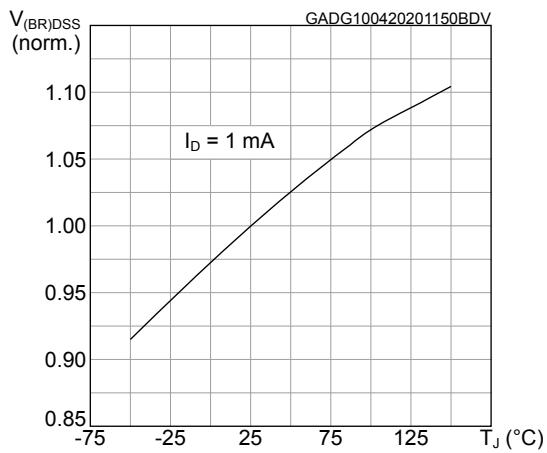
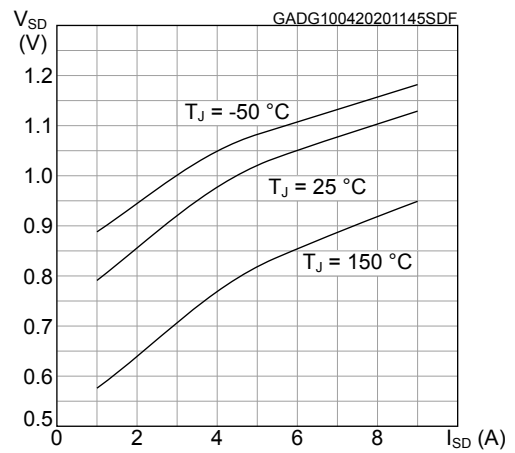
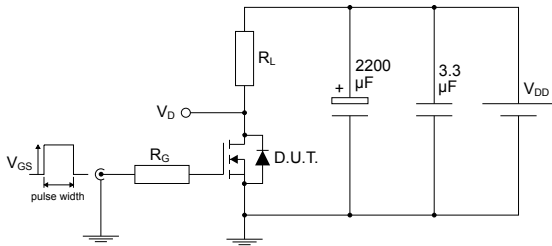


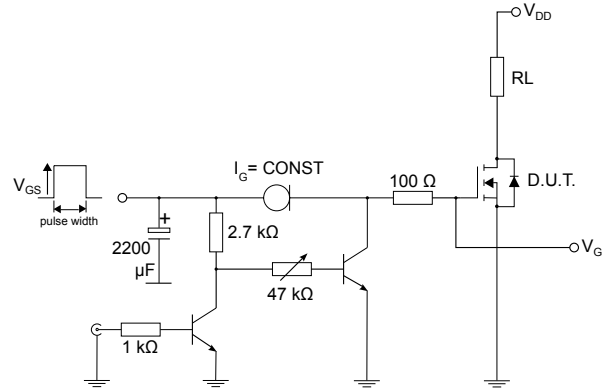
Figure 12. Typical reverse diode forward characteristics



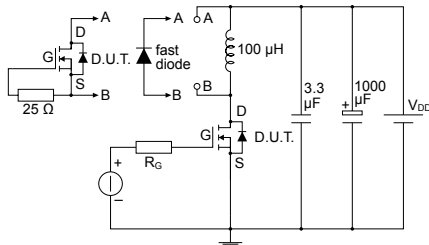
3 Test circuits

Figure 13. Test circuit for resistive load switching times


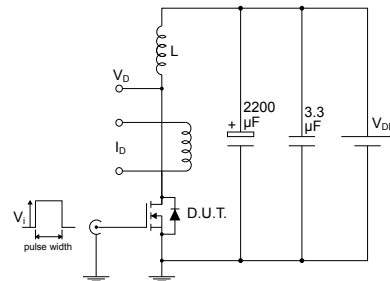
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Figure 14. Test circuit for gate charge behavior


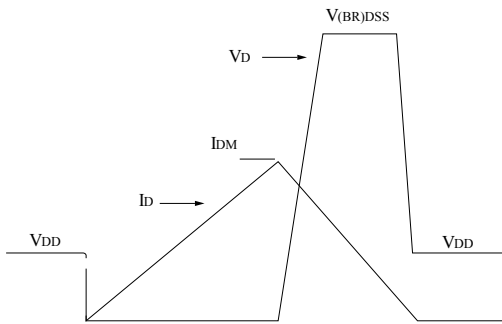
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Figure 15. Test circuit for inductive load switching and diode recovery times


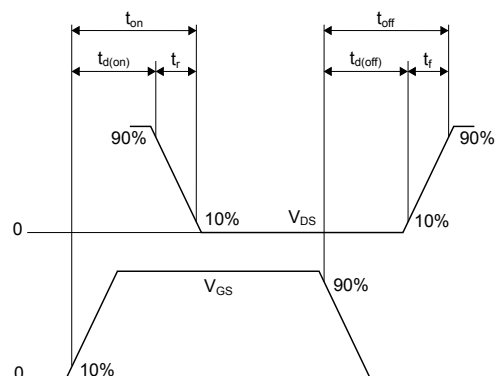
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Figure 16. Unclamped inductive load test circuit


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Figure 17. Unclamped inductive waveform


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Figure 18. Switching time waveform


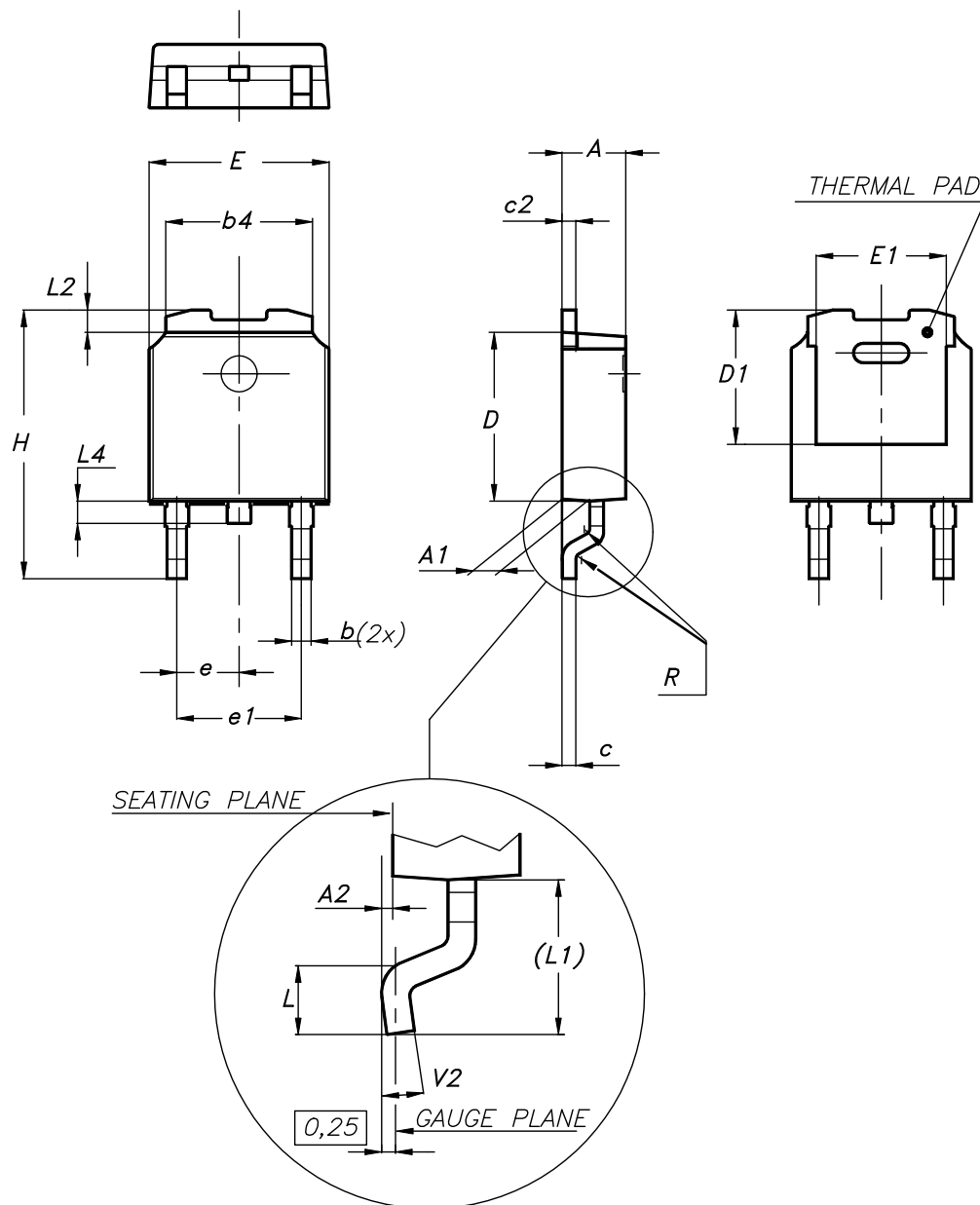
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 DPAK (TO-252) type A package information

Figure 19. DPAK (TO-252) type A package outline

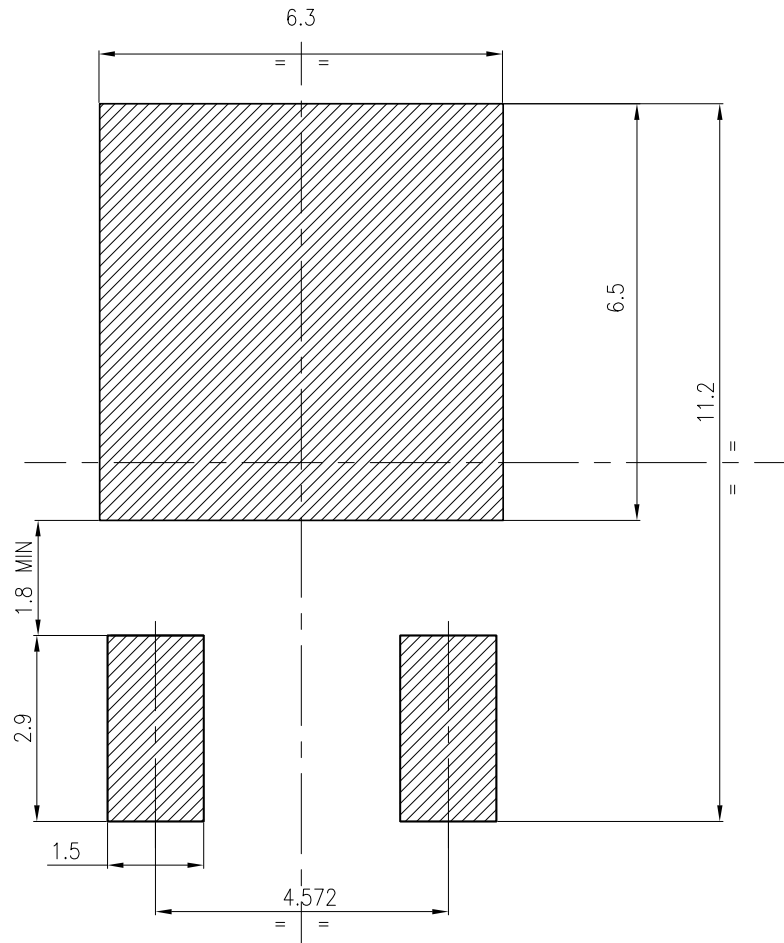


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Table 8. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

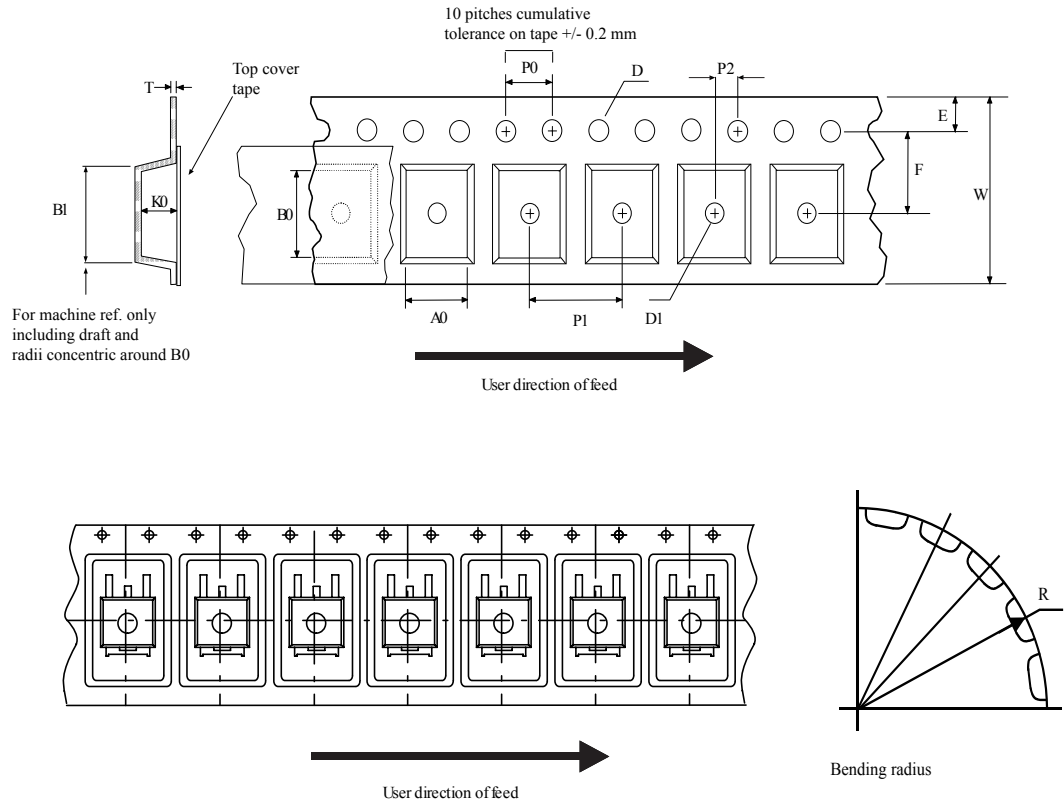
Figure 20. DPAK (TO-252) type A recommended footprint (dimensions are in mm)



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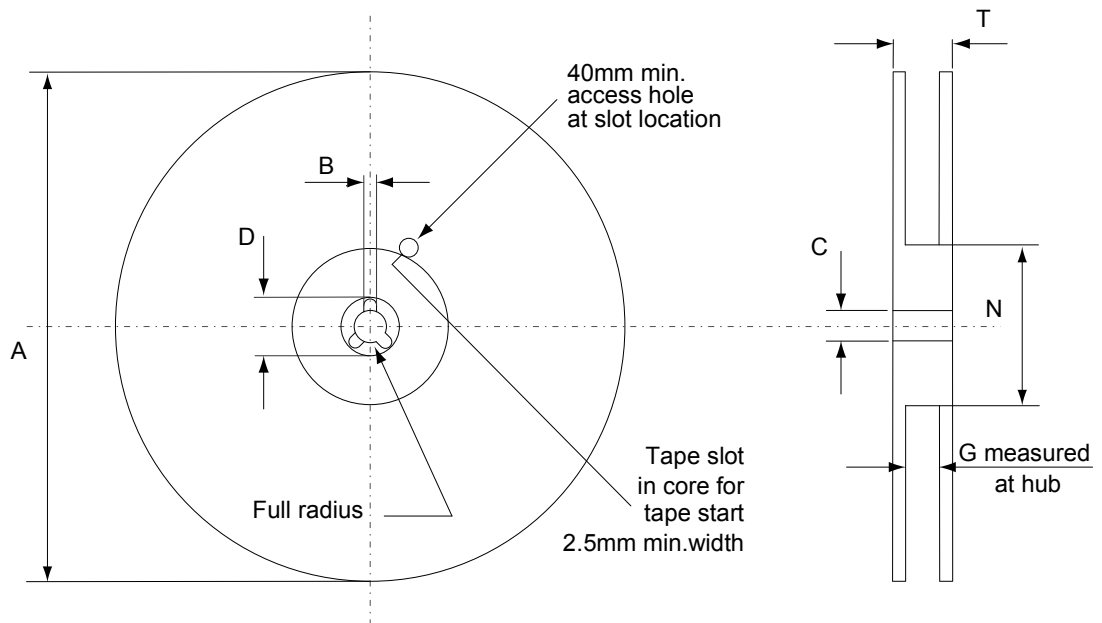
4.2 DPAK (TO-252) packing information

Figure 21. DPAK (TO-252) tape outline



AM08852v1

Figure 22. DPAK (TO-252) reel outline



AM06038v1

Table 9. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Revision history

Table 10. Document revision history

Date	Revision	Changes
17-Apr-2020	1	First release.

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